

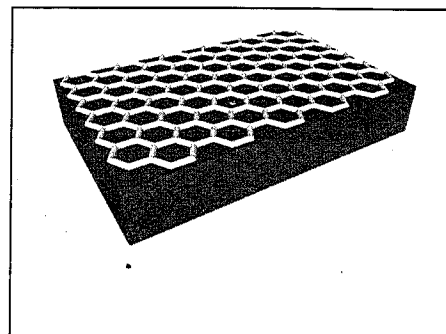


**Transfer-free, direct growth of graphene by atomic layer deposition on oxide surface**

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**Experience:**

[http://www.mse.ntu.edu.tw/index.php?option=com\\_zoo&task=item&item\\_id=47&Itemid=902&lang=tw](http://www.mse.ntu.edu.tw/index.php?option=com_zoo&task=item&item_id=47&Itemid=902&lang=tw)



**Market Needs:**

**The growth of graphene**

**Our Technology:**

The invention breaks the limitation caused by the conventional graphene preparation methods based on mechanical exfoliation, CVD growth on a metal layer, and SiC sublimation. A transfer-free, direct growth of graphene on oxide surface using atomic layer deposition (ALD) was developed.

**Strength:**

**Transfer-free, direct growth of graphene on oxide surface**

**Competing Products:**

**Chemical Vapor Deposition (CVD)**

**Intellectual Properties:**

**No**

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